# Supporting Information

# Ultrafast Electron and Hole Relaxation Pathways in Few-Layer MoS<sub>2</sub>

*Zhaogang Nie*,<sup>*a*</sup> *Run Long*,<sup>*b,c,d</sup> <i>Jefri S. Teguh*,<sup>*a*</sup> *Chung-Che Huang*,<sup>*e*</sup> *Daniel W. Hewak*,<sup>*e*</sup> *Edwin K. L. Yeow*,<sup>*a*</sup> *Zexiang Shen*,<sup>*f,g,h*</sup> *Oleg V. Prezhdo*,<sup>*b\**</sup> *and Zhi-Heng Loh*<sup>*a,f\**</sup></sup>

<sup>a</sup> Division of Chemistry and Biological Chemistry, School of Physical and Mathematical Sciences, Nanyang Technological University, Singapore 637371, Singapore

<sup>b</sup> Department of Chemistry, University of Southern California, Los Angeles, California 90089, United States

<sup>c</sup> School of Physics, Complex Adaptive Systems Laboratory, University College Dublin, Belfield, Dublin 4, Ireland

<sup>d</sup> College of Chemistry, Key Laboratory of Theoretical & Computational Photochemistry of Ministry of Education, Beijing Normal University, Beijing, 100875, P. R. China.

<sup>e</sup> Optoelectronics Research Centre, University of Southampton, Southampton SO17 1BJ, United Kingdom

<sup>f</sup> Division of Physics and Applied Physics, School of Physical and Mathematical Sciences, Nanyang Technological University, Singapore 637371, Singapore

<sup>g</sup> Centre for Disruptive Photonic Technologies, School of Physical and Mathematical Sciences, Nanyang Technological University, Singapore 637371, Singapore

<sup>h</sup> Division of Materials Technology, School of Materials Science and Engineering, Nanyang Technological University, Singapore 639798, Singapore

<sup>\*</sup> Corresponding Authors: (O.V.P.) E-mail: prezhdo@usc.edu. Telephone: +1 (213) 821-3116. (Z.-H.L.) E-mail: zhiheng@ntu.edu.sg. Telephone: +65 6592-1655.

#### 1. Fit Parameters for Intravalley Electronic Relaxation Dynamics

The temporal evolution of the spectral first moment  $\langle \lambda^{(1)}(t) \rangle$  computed about the exciton B transition is fit to a Gaussian decay function of the form

$$\langle \lambda^{(1)}(t) \rangle = \Delta \lambda \ e^{-t^2/2\left(\tau_e^{(1)}\right)^2} + \lambda_0 \tag{S1}$$

where  $\Delta \lambda$  is the amplitude of the blueshift,  $\tau_e^{(1)}$  is the Gaussian decay time, and  $\lambda_0$  is the offset wavelength. The fit parameters are summarized in Table S1 below.

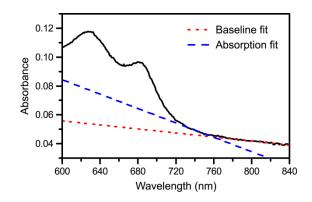
| Fluence (mJ/cm <sup>2</sup> ) | <b>Δ</b> λ (nm) | $	au_e^{(1)}$ (ps) | $\lambda_0$ (nm) |
|-------------------------------|-----------------|--------------------|------------------|
| 0.06                          | $21.4\pm0.7$    | $1.77\pm0.08$      | $602.2\pm0.6$    |
| 0.14                          | $20.9\pm0.2$    | $1.34\pm0.02$      | $602.4\pm0.1$    |
| 0.29                          | $13.3\pm0.1$    | $1.34\pm0.02$      | $610.4\pm0.1$    |

**Table S1.** Fit parameters extracted from  $\langle \lambda^{(1)}(t) \rangle$ .

From the above, it is seen that the offset wavelength  $\lambda_0$  increases with excitation fluence. This trend is consistent with increased band gap renormalization at larger carrier densities, resulting in a decrease in the band gap with increasing carrier density.

#### 2. Calculation of the Excess Energies of the Carriers

The excess energies of the carriers are calculated by first determining the threshold wavelength for the direct-gap optical absorption at the K valley. The threshold wavelength is ascertained to be 759 nm from the linear fits to the baseline and the absorption peak (Figure S1). Given that the absorption maximum of the exciton A transition resides at 684 nm, the total excess energy of the carriers is therefore 1440 cm<sup>-1</sup>. By employing the  $m_e^*/m_h^*$  ratio of 1.76 obtained from first-principles electronic structure calculations,<sup>1</sup> the excess energies of the electron and hole are calculated to be  $620 \pm 230$  and  $820 \pm 290$  cm<sup>-1</sup>, respectively. The relatively large error margins arise from the presence of an exponentially decaying absorption feature in the long wavelength region that is due to indirect transitions. This long-wavelength absorption tail introduces uncertainty in determining the appearance threshold of the absorption peak.



**Figure S1.** Determination of the threshold wavelength for the direct-gap optical absorption of the five-layer  $MoS_2$  sample. The optical absorption spectrum acquired at 300 K is shown as the solid line. The threshold wavelength is given by the intersection between the linear fits to the baseline (dotted line) and to the absorption peak (dashed line).

#### 3. Reconstructed transmission spectrum of the pure photoexcited sample

The differential transmission signal  $\Delta T/T$  is directly obtained by measuring the transmitted intensity of the probe with  $(I_{on})$  and without  $(I_{off})$  the pump beam. That is,

$$\Delta T/T = (I_{on} - I_{off})/I_{off}.$$
(S1)

To reconstruct the transmission spectrum of the pure photoexcited species  $T_e$ , one requires knowledge of the excitation fraction f and the intensity of the probe beam before the sample  $(I_0)$ . While the former can be determined, the latter is not usually measured in the experiments. Nevertheless,  $T_e$  can be reconstructed from the measured  $\Delta T/T$  spectrum and an independently measured ground-state sample transmission spectrum T by employing the expression

$$T_e = T \left(\frac{\Delta T}{T} + 1\right)^{1/f}.$$
(S2)

The above procedure is used to reconstruct the transmission spectrum of the pure photoexcited species that is produced by the excitation of five-layer MoS<sub>2</sub> sample at 300 K with a pump fluence of 0.29 mJ/cm<sup>2</sup> (see Fig. 6c of the main text). The resultant transmission spectrum is dominated by a  $T_e > 1$  feature (Fig. S2), which is consistent with probe pulse-induced stimulated emission. However, it is important to note that the absolute value of  $T_e$  is highly sensitive to the excitation fraction f, which itself is challenging to quantify accurately. The  $T_e$  spectrum should therefore be analyzed only qualitatively.

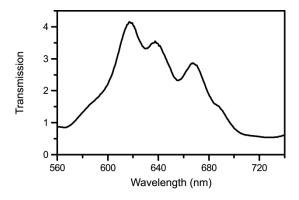


Figure S2. Reconstructed transmission spectrum of the pure photoexcited species at a time delay of 200 fs following excitation of the five-layer  $MoS_2$  sample at 300 K with a pump fluence of 0.29 mJ/cm<sup>2</sup>.

#### 4. Resonant Raman Spectrum of Five-Layer MoS<sub>2</sub>

The resonant Raman spectrum of the five-layer MoS<sub>2</sub> sample is recorded at 295 K on a Horiba LabRAM HR instrument with 632.8-nm irradiation. The Raman spectrum and its second derivative spectrum are shown in Figure S3.

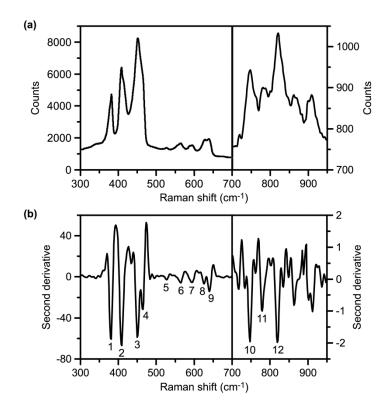


Figure S3. (a) Resonant Raman spectrum for the five-layer  $MoS_2$  sample and (b) its secondderivative spectrum.

The labeled peaks in the second-derivative spectrum are assigned according to previous reports in the literature.<sup>2-4</sup> The assignment is given in Table S2 below.

**Table S2.** Assignment of peaks observed in the resonant Raman spectrum of five-layer  $MoS_2$ . The peak numbers are used to identify the negative-valued minima observed in the second-

| Peak No. | Frequency (cm <sup>-1</sup> ) | Assignment                        |
|----------|-------------------------------|-----------------------------------|
| 1        | 381                           | $E_{2g}^{1}(\Gamma)$              |
| 2        | 409                           | $A_{1g}(\Gamma)$                  |
| 3        | 450                           | 2LA(M)                            |
| 4        | 465                           | $A_{2u}(\Gamma)$                  |
| 5        | 528                           | $E_{1g}(M) + LA(M)$               |
| 6        | 565                           | $2E_{1g}(\Gamma)$                 |
| 7        | 594                           | $E_{2g}^{1}(\Gamma) + LA(M)$      |
| 8        | 626                           | unknown                           |
| 9        | 640                           | $A_{1g}(M) + LA(M)$               |
| 10       | 747                           | $2E_{2g}^{1}(M)$                  |
| 11       | 779                           | $A_{1g}(M) + E_{2g}^1(M)$         |
| 12       | 819                           | $2A_{1g}(\Gamma)$ or $2A_{1g}(M)$ |

derivative spectrum (Figure S2b).

The unknown peak at  $626 \text{ cm}^{-1}$  was also observed in earlier resonant Raman measurements of few-layer MoS<sub>2</sub> samples,<sup>4</sup> although its origin remains unknown.

### 5. Measured Optical Pump-Probe Cross-Correlation

The time resolution of the experimental apparatus is measured by performing a second-order pump-probe intensity cross-correlation with a  $10-\mu$ m-thick BBO crystal located at the sample position. The resultant cross-correlation trace yields a full-width at half-maximum (FWHM) of 83 fs (Figure S4).

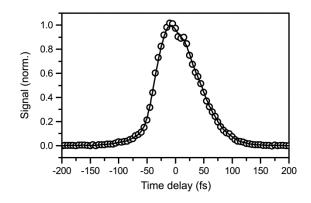


Figure S4. Cross-correlation trace of the pump and probe pulses. The FWHM is 83 fs.

#### 6. Pump Fluence-Dependence Measurements

Pump fluence-dependence measurements were performed to verify that photoexcitation of the sample occurs in the linear regime. Figure S5 shows a log-log plot of the peak  $\Delta T/T$  signal *S* obtained at the B exciton transition as a function of fluence *F*. Because  $S \propto F^N$ , the slope of the log-log plot yields the photon order *N*, which in this case is found to be  $1.05 \pm 0.06$ . This result confirms that excitation of the MoS<sub>2</sub> sample under our experimental conditions occurs in the linear regime.

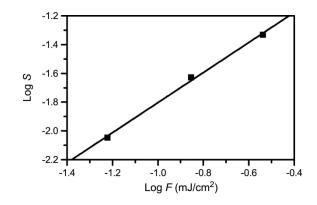


Figure S5. Dependence of the maximum  $\Delta T/T$  signal on the pump fluence, confirming onephoton excitation of the sample.

## References

- 1. Qiu, D. Y.; da Jornada, F. H.; Louie, S. G. Optical Spectrum of MoS<sub>2</sub>: Many-Body Effects and Diversity of Exciton States. *Phys. Rev. Lett.* **2013**, *111*, 216805.
- Chen, J. M.; Wang, C. S. Second Order Raman Spectrum of MoS<sub>2</sub>. *Solid State Commun.* 1974, 14, 857–860.
- Stacy, A. M.; Hodul, D. T. Raman Spectra of IVB and VIB Transition Metal Disulfides Using Laser Energies Near the Absorption Edges. *J. Phys. Chem. Solids* 1985, *46*, 405–409.
- 4. Chakraborty, B.; Ramakrishna Matte, H. S. S.; Sood, A. K.; Rao, C. N. R. Layer-Dependent Resonant Raman Scattering of a Few Layer MoS<sub>2</sub>. *J. Raman Spectrosc.* **2013**, *44*, 92–96.